

DIRECT INTERELECTRODE CAPACITANCES

Section No. 1

Grid to Plate	0.28 pf
Input: g to $(h + 1k + 1g_2 + 1g_3 + 1S)$	12.0 pf
Output: p to $(h + 1k + 1g_2 + 1g_3 + 1S)$	7.0 pf

Section No. 2

Grid No. 1 to Plate (Max.)	0.40 pf
Grid No. 3 to Plate	3.2 pf
Grid No. 1 to $(h + 2k + 2g_2 + 2g_3 + 1S)$	7.0 pf
Grid No. 3 to $(h + 2k + 2g_2 + 2g_3 + 2p + 1S)$	8.0 pf
Grid No. 1 to Grid No. 3	0.15 pf
Plate No. 1 to Plate No. 2	0.18 pf

RATINGS (Design Maximum Rating System)

Section No. 1

Plate Voltage	200 Volts
Screen Voltage	150 Volts
Plate Dissipation	10 Watts
Screen Dissipation	1.8 Watts
DC Cathode Current	65 Ma
Grid No. 1 Circuit Resistance	
Cathode Bias	1.0 Megohms

Section No. 2

Plate Voltage	300 Volts
Suppressor Voltage	25 Volts
Screen Supply Voltage	300 Volts
Positive DC Grid Voltage	0 Volt
Plate Dissipation	1.7 Watts
Screen Dissipation	1.0 Watts

AVERAGE CHARACTERISTICS

Section No. 1, Class A1 Amplifier

Plate Voltage	170 Volts
Screen Voltage	140 Volts
Grid No. 1 Voltage	-3.0 Volts
Peak AF Grid Voltage	15 Volts
Plate Resistance (Approx.)	33,000 Ohms
Transconductance	4900 μ mhos
Zero Signal Plate Current	74 Ma
Maximum Signal Plate Current	76 Ma
Zero Signal Screen Current	3.9 Ma
Maximum Signal Screen Current	8.3 Ma
Load Resistance	2500 Ohms
Total Harmonic Distortion (Approx.)	10 Percent
Maximum Signal Power Output	4.0 Watts

Section No. 2

Plate Voltage	150 Volts
Suppressor Voltage	0 Volt
Screen Voltage	100 Volts
Cathode Resistor	180 Ohms
Plate Resistance (Approx.)	110,000 Ohms
Transconductance (G_1)	2500 μ mhos
Transconductance (G_3)	850 μ mhos
Plate Current	1.3 Ma
Screen Current	2.1 Ma
E_{c1} for $I_b = 20 \mu a$	-4.0 Volts
E_{c3} for $I_b = 50 \mu a$	-3.0 Volts

DAMPER

6BZ3

17BZ3

Heater-Cathode Diode

Construction.....Compactron T-9
 BaseButton 12 Pin, E12-70
 Basing12FX
 Outline9-60
 Maximum Diameter1.188 In.
 Maximum Seated Height2.500 In.
 Maximum Overall Height2.875 In.

